

Pictures to: 4. IBM T.J. Watson Research Center

4.3.1 Pictures to Anodic Defect Etching

As before, O will supply the pictures in the two publications plus a number of auxiliary ones never published before.

First, the two pictures in the letter (ref. 24)

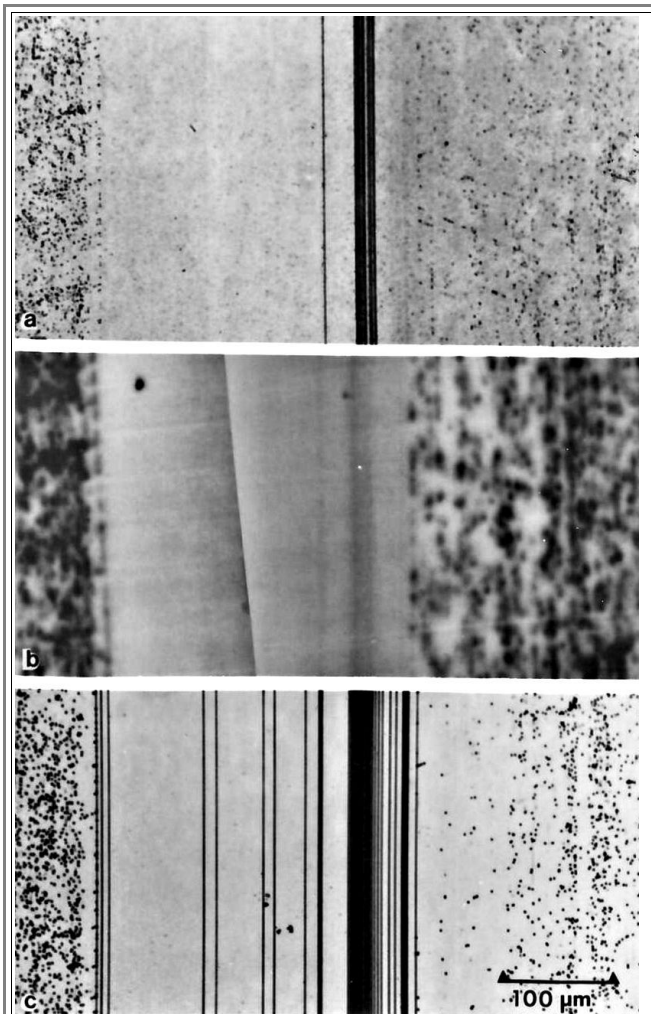


Fig. 1 In Publication 24

(a) Si ribbon anodically etched at -0.4 V. (b) EBIC image of adjacent area, (c) adjacent area etched at $+0.4$ V.

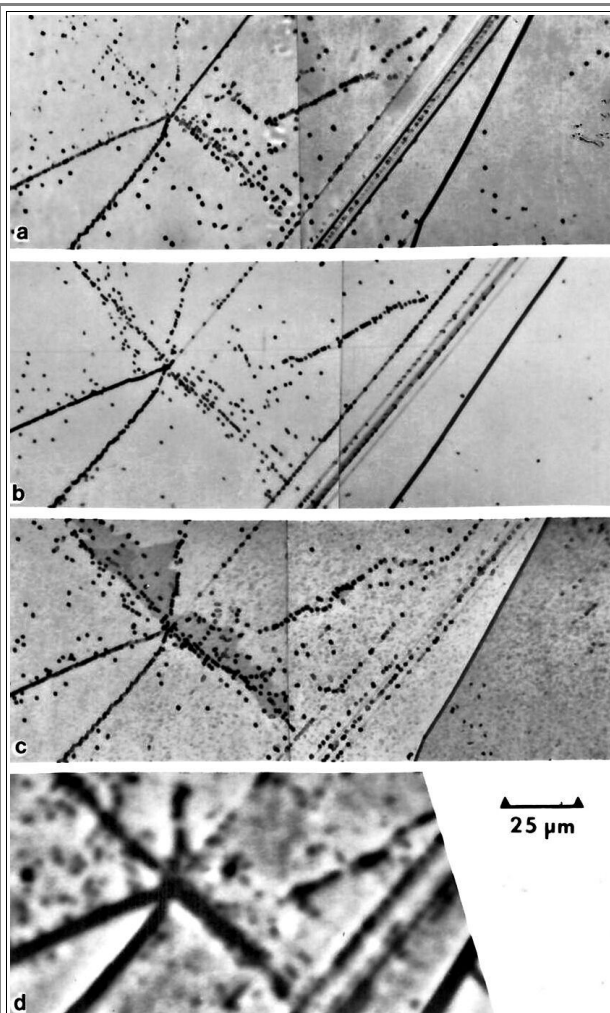
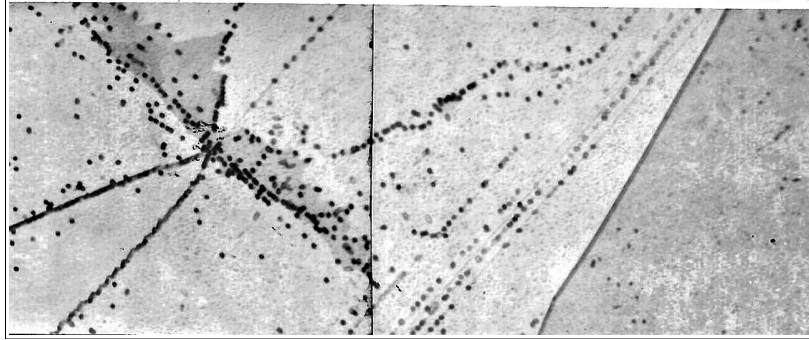
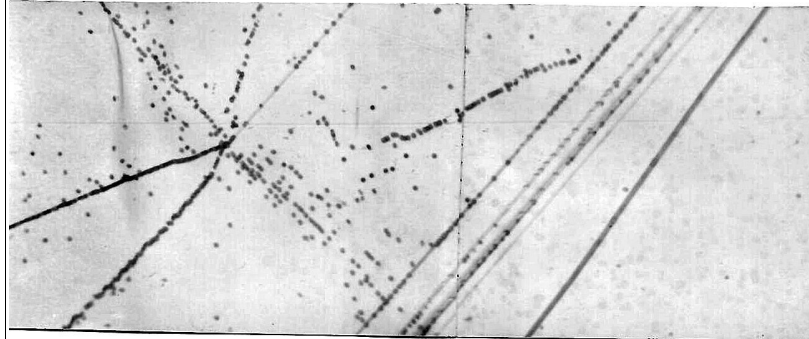
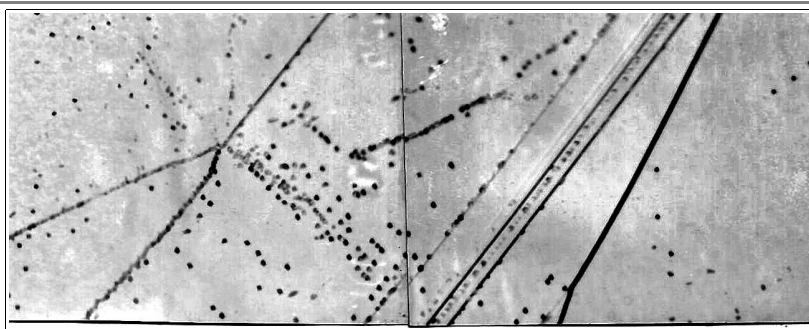


Fig. 2 In Publication 24

Same area in polycrystalline ASilicon etched chemically (a), anodically at at + 0.4 V. anodically at – 0.4 V(c).

Fig. 2(d) shows the EBIC image of this area.



.Parts of Fig. 2 in large format
(Click to enlarge)

The pictures from the full paper (ref, 22) follow

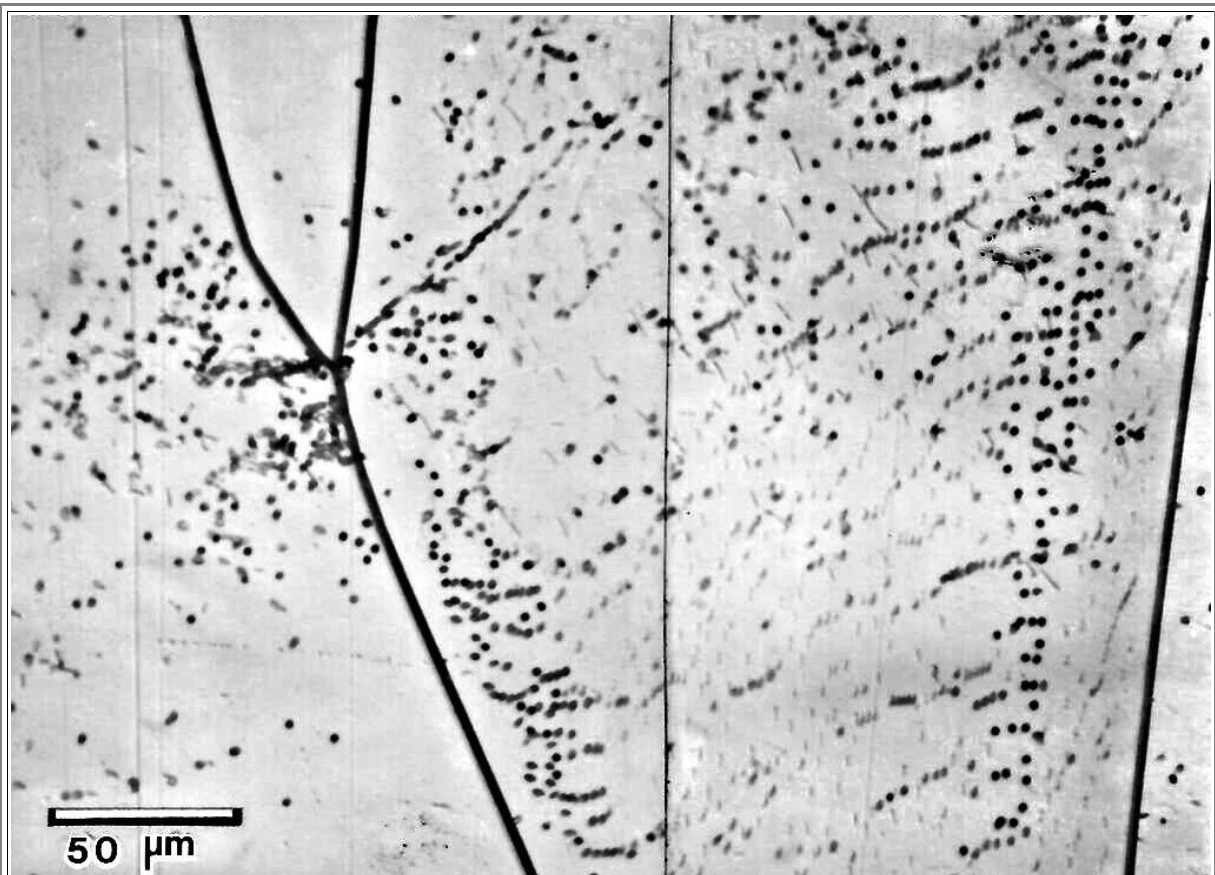


Fig. 2 in ref.22

Fig. 2. Example of anodically etched poly-Si (40 min at OV bias)

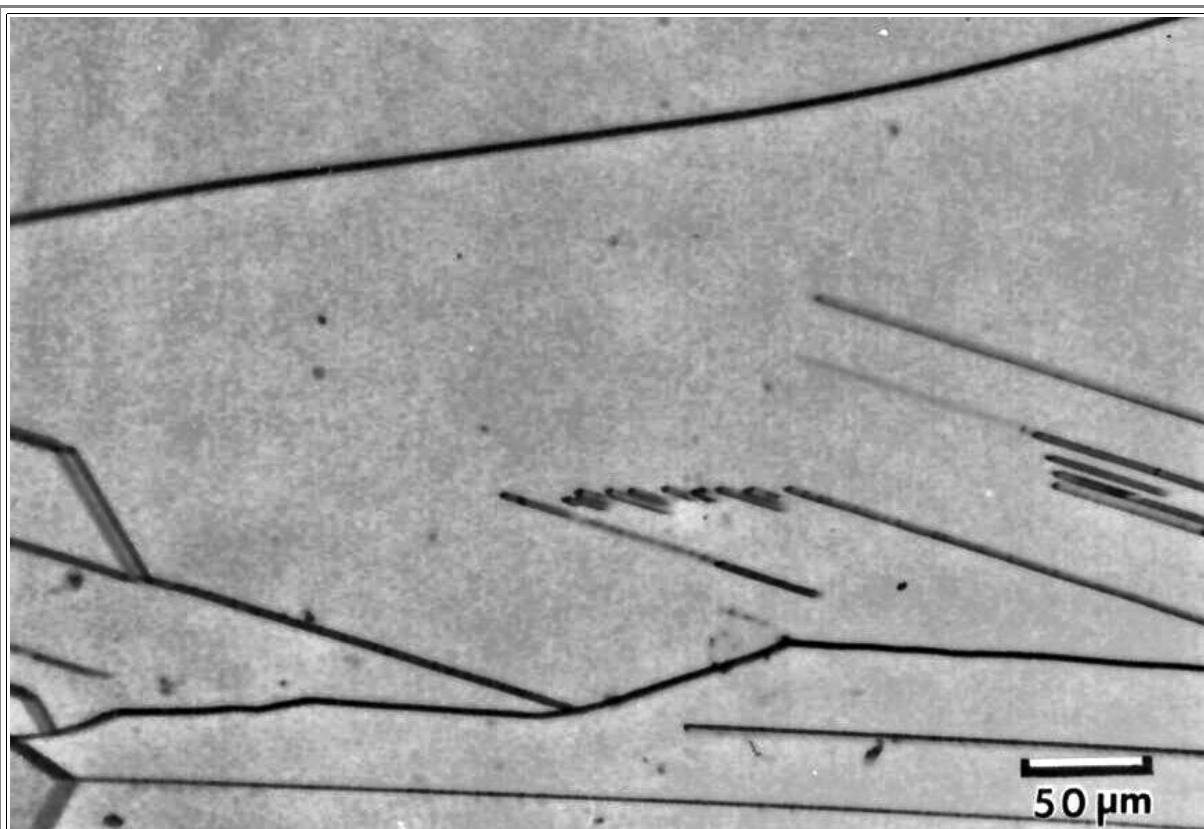


Fig. 3 In Publication 1.

Fig. 4 In Publication 1

Fig. 5 In Publication 1.

Fig. 6 In Publication 1

Fig. 7 In Publication 1.

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Auxiliary to Fig. 10 In Publication 1.

Fig. 10 in Publication 1.